

Supporting Information for

Transition Metal-doped Metal Oxide
Nanocrystals: Efficient Substitutional Doping
Through a Continuous Growth Process

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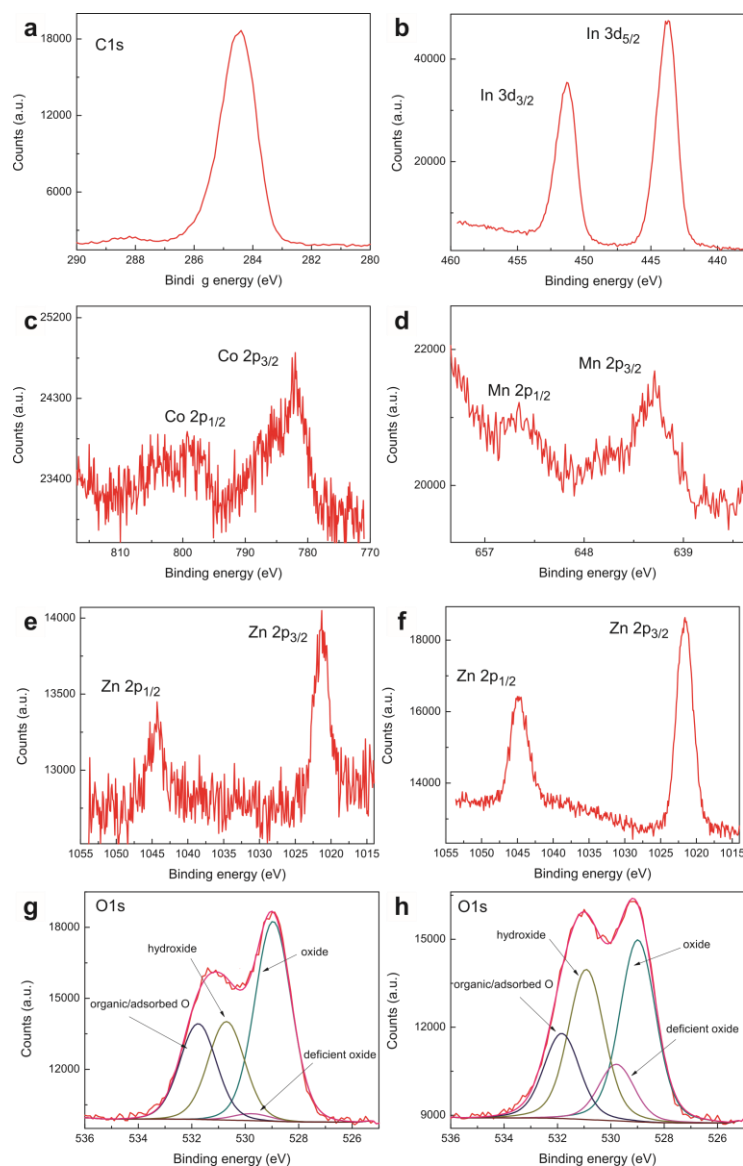


Figure S1. XPS spectra of doped In_2O_3 nanocrystals. Compositions shown in Table 3 of the manuscript are calculated based on integration of the $\text{In } 3d_{5/2}$ and dopant $2p_{3/2}$ peak. **a)** displays a typical C1s spectra and **b)** a typical $\text{In } 3d$ spectra of the doped and undoped nanocrystals. **c)** and **d)** show the Co and $\text{Mn } 2p$ spectra from $\text{Co: In}_2\text{O}_3$ and $\text{Mn: In}_2\text{O}_3$ respectively. **e)** and **f)** display the $\text{Zn } 2p$ region of 5% $\text{Zn: In}_2\text{O}_3$ and 20% $\text{Zn: In}_2\text{O}_3$, respectively. **g)** displays the O1s spectra from 5% $\text{Zn: In}_2\text{O}_3$, and **h)** 20% $\text{Zn: In}_2\text{O}_3$. The O1s spectra shown in **g)** and **h)** can be fit to four peaks of the same peak shape and a width of 1.5 eV; the peak at 529.0 eV corresponds to oxide in In_2O_3 , the peak 0.7 eV greater corresponds to oxygen deficient/defect oxide, the peak at 530.9 eV corresponds to hydroxide, and the peak at 531.8 eV corresponds to adsorbed oxygen and organic oxygen in the ligand shell.^{1–5} The increase in dopant atom concentration likely leads to the increase in oxygen vacancy formation, which is displayed in **g)** and **h)**. Spectra are referenced to the C1s hydrocarbon peak at 284.5 eV.

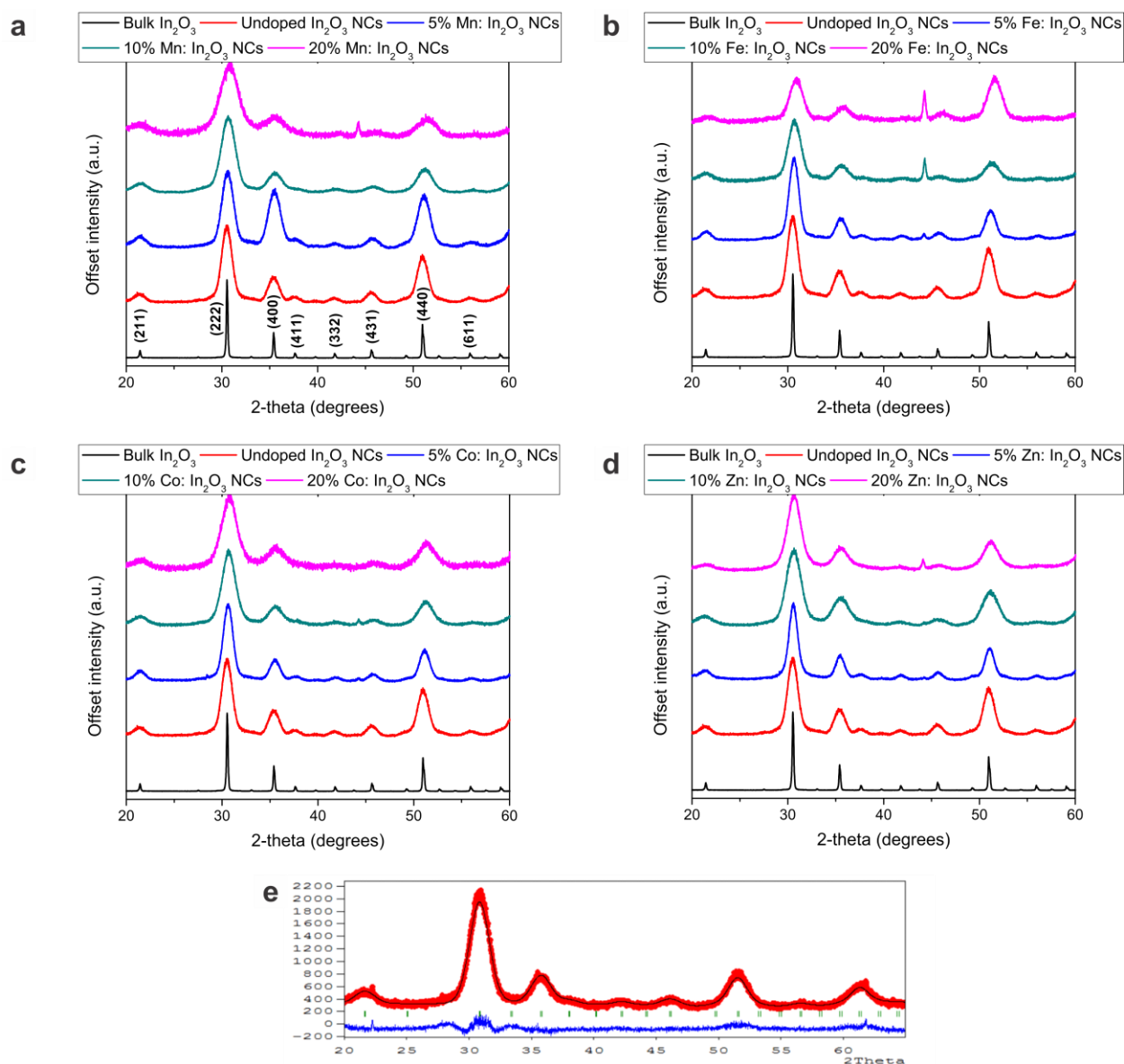


Figure S2. Raw XRD patterns acquired from undoped and doped In_2O_3 nanocrystals at varying dopant concentrations, re-plotted from Figure 2 in the manuscript: **a)** Mn: In_2O_3 **b)** Fe: In_2O_3 **c)** Co: In_2O_3 **d)** Zn: In_2O_3 . The peak present at 43.5° in some samples is due to the silicon substrate. All acquired patterns match that of cubic In_2O_3 (bulk pattern shown in black in each plot). **e)** Displays a typical Rietveld refinement using Fullprof Suite.⁶ Background points were picked by hand, and peaks were fit using a pseudo-Voigt profile. Once scale, zero offsets, and peak shape were refined, lattice parameters were allowed to optimize. In XRD patterns where the substrate peak is present, an exclusion zone in the refinement was added to prevent model optimization from $43\text{--}44^\circ$.

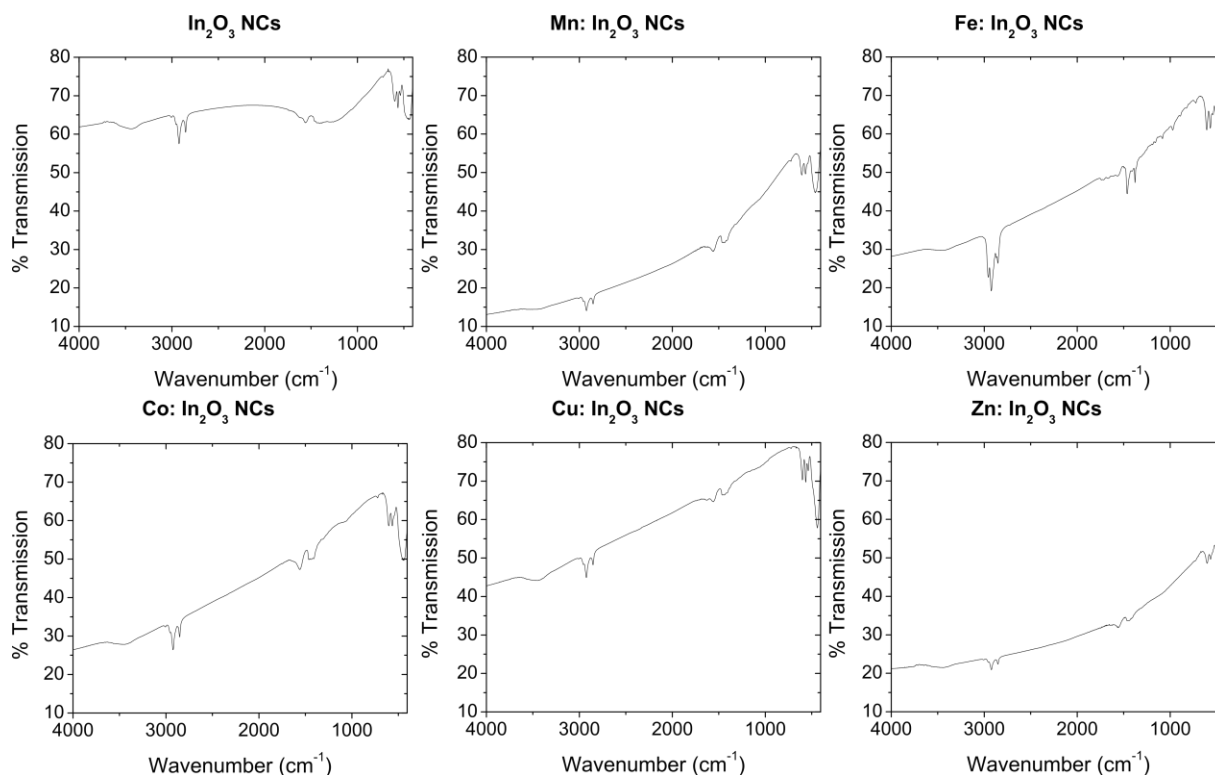


Figure S3. FTIR spectra obtained from undoped and doped In_2O_3 nanocrystals. Unlike the undoped nanocrystals (top left), which display a weak plasmon resonance $\sim 1400\text{ cm}^{-1}$, the doped nanocrystals display much stronger plasmon absorbances centered at energies $> 4000\text{ cm}^{-1}$. The strong absorbance and the shift of the LSPR to higher energies is an indication of an increased concentration of oxygen vacancy formation.

References:

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